

FGW40N120W

Discrete IGBT

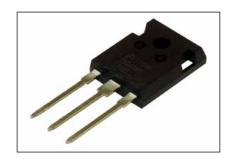
Discrete IGBT (High-Speed W series) 1200V / 40A

■ Features

Low power loss Low switching surge and noise High reliability, high ruggedness (RBSOA, SCSOA etc.)

Applications

Uninterruptible power supply PV Power coditionner Inverter welding machine

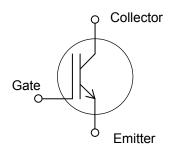


■ Maximum Ratings and Characteristics

● Absolute Maximum Ratings (at T_c=25°C unless otherwise specified)

Items	Symbols	Characteristics	Units	Remarks
Collector-Emitter Voltage	Vces	1200	V	
Gate-Emitter Voltage	V _{GES}	±20	V	
DC Collector Current	Ic@25	65	Α	Tc=25°C, Tj=150°C
	Ic@100	40	Α	Tc=100°C, Tj=150°C
Pulsed Collector Current	I _{CP}	160	Α	Note *1
Turn-Off Safe Operating Area	-	160	Α	Vce≤1200V, Tj≤175°C
Short Circuit Withstand Time	tsc	5	μs	Vcc≤600V, VcE=15V Tj≤150°C
IGBT Max. Power Dissipation	P□	430	W	Tc=25°C
Operating Junction Temperature	T _j	-40 ~ +175	°C	
Storage Temperature	T _{stg}	-55 ~ +175	ç	

■ Equivalent circuit



Note *1 : Pulse width limited by Tjmax.

● Electrical characteristics (at T_j= 25°C unless otherwise specified)

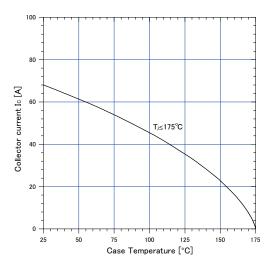
Description	Cumbala	Conditions		Characteristics			Units	
Description	Symbols			min.	typ.	max.	Units	
Zero Gate Voltage Collector Current	I	V _{CE} = 1200V, V _{GE} = 0V	T _j =25°C	-	-	250	μΑ	
Zero Gate Voltage Collector Current	Ices	VGE = 1200V, VGE = 0V	T _j =175°C	-	-	2	mA	
Gate-Emitter Leakage Current	IGES	$V_{CE} = 0V$, $V_{GE} = \pm 20V$		-	-	200	nA	
Gate-Emitter Threshold Voltage	V _{GE (th)}	$V_{CE} = +20V$, $I_{C} = 40mA$		5.0	6.0	7.0	V	
Collector-Emitter Saturation Voltage	V _{CE} (sat)	V _{GE} = +15V, I _C = 40A	T _i =25°C T _i =175°C	1.4	2.0	2.6	V	
Input Capacitance	Cies	V _{CE} =25V	10, 110 0	1250	2500	3750		
Output Capacitance	Coes	V _{GE} =0V			110	165	pF	
Reverse Transfer Capacitance	Cres	f=1MHz		17	34	51		
Gate Charge	Q _G	V _{CC} = 400V I _C = 40A V _{GE} = 15V		60	120	180	nC	
Turn-On Delay Time	t _{d(on)}	T _j = 25°C		16	32	48		
Rise Time	tr	Vcc = 600V		27	54	81		
Turn-Off Delay Time	t _{d(off)}	Ic = 40A		89	178 267 ns		115	
Fall Time	t	V _{GE} = 15V		20	40	60		
Turn-On Energy	Eon	$R_G = 10\Omega$		1.4	2.8	4.2		
Turn-Off Energy	Eoff	L = 500µH Energy loss include "tail" and FWD (FDRW20S120J) reverse recovery.		0.8	1.6	2.4	mJ	
Turn-On Delay Time	t _{d(on)}	T _i = 150°C		16	32	48		
Rise Time	t	Vcc = 600V		24	48	72	no	
Turn-Off Delay Time	t _{d(off)}	Ic = 40A		110	220	330	ns	
Fall Time	tr	V _{GE} = 15V		28	56	84		
Turn-On Energy	Eon	$R_G = 10\Omega$		2.3	4.6	6.9		
Turn-Off Energy	Eoff	L = 500µH Energy loss include "tail" a (FDRW20S120J) reverse		1.2	2.4	3.6	mJ	

● Thermal resistance characteristics

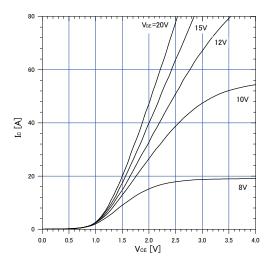
Items	Symbols Conditions	Conditions	Characteristics			Units
		Conditions	min.	typ.	max.	Units
Thermal Resistance, Junction-Ambient	R _{th(j-a)}	-	-	-	50	°C/W
Thermal Resistance, Junction to Case	R _{th(j-c)_IGBT}	-	-	-	0.347	C/VV

■ Characteristics (Representative)

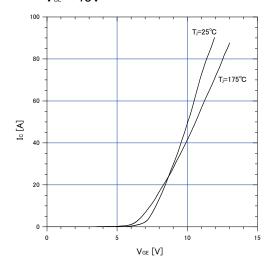
Graph.1 DC Collector Current vs T_c $V_{ce} \ge +15V$, $T_i \le 175$ °C



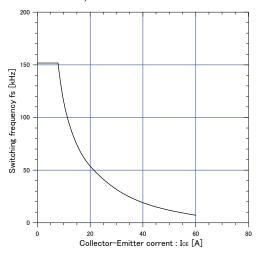
Graph.3
Typical Output Characteristics (Voe-lo)
T_i=25°C



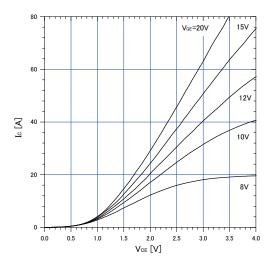
Graph.5
Typical Transfer Characteristics
V_{se}=+15V



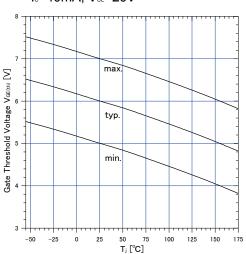
Graph.2 Collector Current vs. switching frequency V_{ce} =+15V, T_{c} ≤175°C, V_{cc} =600V, D=0.5, R_{e} =10 Ω , T_{c} =100°C



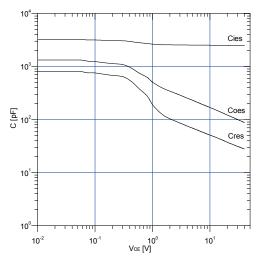
Graph.4 Typical Output Characteristics (V_{ce} - I_c) T_j =175°C



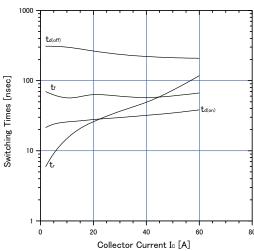
Graph.6
Gate Threshold Voltage vs. T₁
I₀=40mA, V₀∈=20V



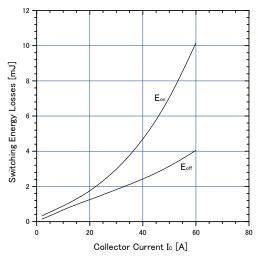
Graph.7 Typical Capacitance V_e=0V,f=1MHz,T,=25°C



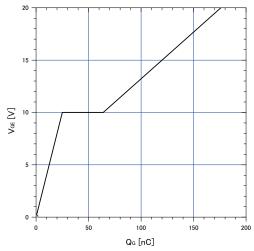
Graph.9 Typical switching time vs. I_c T_i=175°C,V_{cc}=600V,L=500 μ H V_{cE}=15V,R_c=10 Ω



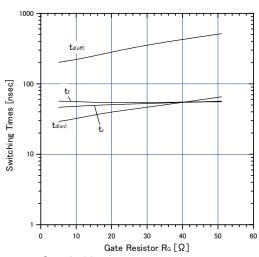
Graph.11 Typical switching losses vs. Io $T_{\rm J}$ =175°C, $V_{\rm cc}$ =600V,L=500 μ H $V_{\rm ce}$ =15V, $R_{\rm c}$ =10 Ω



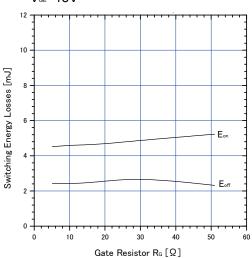
Graph.8 Typical Gate Charge Vcc=600V,Ic=40A,T,=25°C



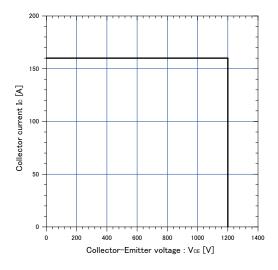
Graph.10 Typical switching time vs. R_s T_i=175°C,V_{cc}=600V,I_c=40A,L=500 μ H V_{se}=15V



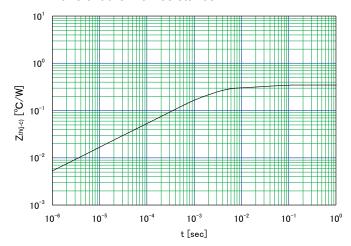
Graph.12
Typical switching losses vs. R_o
T_i=175°C,V_{oc}=600V,I_o=40A,L=500μH
V_{oe}=15V



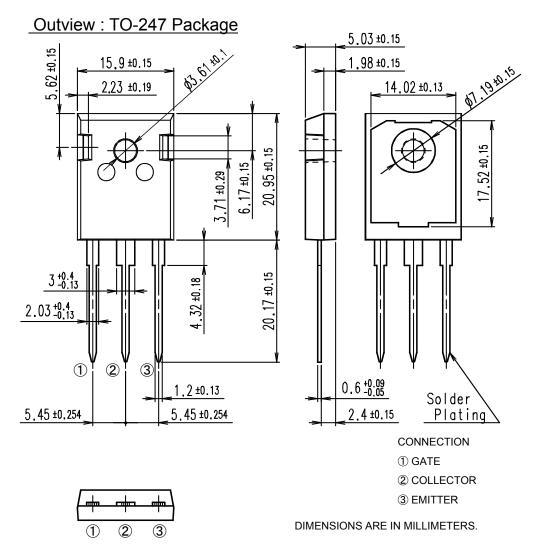
Graph.13 Reverse biased Safe Operating Area T_i≤175°C,V_e=+15V/0V,R_e=10Ω



Graph.14
Transient thermal resistance



■ Outline Drawings, mm



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